Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	(US-20030173641-\$ or US-20030181019-\$ or US-20040021197-\$ or US-20040115897-\$ or US-20030020117-\$).did. or (US-6642125-\$ or US-6486517-\$ or US-6482715-\$ or US-6770530-\$ or US-6313011-\$).did.	US-PGPUB; USPAT	OR	ON	2007/10/31 08:56
L2	242	438/218.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:16
L3	237	438/248.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:16
L4	1098	(trench with isolation with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:38
L5	291	L4 and (trench with isolation).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:38
L6	95	L5 and (p adj (type or channel)) and (n adj (type or channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:38
L7	45	L6 and (liner or barrier).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:44

L8	0	((trench with isolation with region) and (first with mask) and (etch\$3 with mask) and (trenches with substrate) and (second with mask) and (second with (side adj wall)) and (first with type with liner) and (second with type with liner).and (disposed with directly with walls)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:47
L9	0	((trench with isolation with region) and (first with mask) and (etch\$3 with mask) and (trenches with substrate) and (second with mask) and (second with (side adj wall)) and (first with type with liner) and (second with type with liner) and (disposed with directly with walls))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:47
S1	485	(trench with isolation with region with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/05 15:07
S2	124	S1 and ((liner or barrier) with (doped or conductivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 11:17
S3	2	S2 and (strained adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 11:02
S4	25	S2 and (trench\$3).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 11:03
S5	172	S1 and ((liner or barrier)).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/30 11:17
S6	30	S5 and (trench adj isolation).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON ·	2005/11/30 11:17
S7	3	("20020098649" "6482715" "6486517").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/30 11:27
S8	0	("6770530").URPN.	USPAT	OR	ON	2005/11/30 11:28

S9	233	(trench with isolation with region with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall)) and	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 15:45
		((p-type and n-type) or (p-doped and n-doped))				
S10	90	S9 and ((liner or barrier) with thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 15:55
S11	13	S9 and ((liner or barrier) with trench). ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 15:56
S12	150	438/218.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:00
S13	160	438/248.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/07 16:47
S14	134	(trench with isolation with region with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall)) and SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 10:46
S15	6	S14 and (trench and SOI).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 10:46
S16	3	("20020098649" "6482715" "6486517").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/11 15:47
S17	838	(trench with isolation with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/05 15:09
S18	227	S17 and (trench with isolation).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/05 15:09

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S19	67	S18 and (p adj (type or channel)) and (n adj (type or channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/05 15:13
S20	34	S19 and (liner or barrier).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 16:31
S21	1022	(trench with isolation with substrate) and mask and etch\$3 and (first with (liner or barrier)) and (second with (liner or barrier)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 16:31
S22	274	S21 and (trench with isolation).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 16:31
S23	87	S22 and (p adj (type or channel)) and (n adj (type or channel))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/25 16:31
S24	43	S23 and (liner or barrier).ab.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/31 09:38